

MPS2907A Series

General Purpose Transistors

PNP Silicon

Features

- These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	–60	Vdc
Collector – Base Voltage	V_{CBO}	–60	Vdc
Emitter – Base Voltage	V_{EBO}	–5.0	Vdc
Collector Current – Continuous	I_C	–600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

DEVICE MARKING

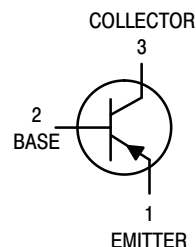
Device	Line 1	Line 2
MPS2907AG	MPS	2907A
MPS2907ARLG	MPS2	907A
MPS2907ARLRAG	MPS	2907
MPS2907ARLRPG	MPS	2907

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

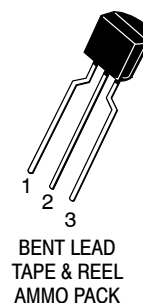
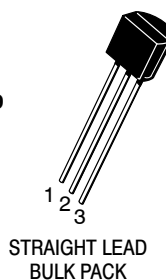


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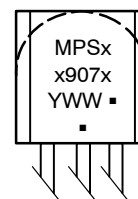
<http://onsemi.com>



TO-92
CASE 29
STYLE 1



MARKING DIAGRAM



Y = Year
WW = Work Week
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MPS2907A Series

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 1) ($I_C = -10\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	-60	–	Vdc	
Collector – Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	-60	–	Vdc	
Emitter – Base Breakdown Voltage ($I_E = -10\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	-5.0	–	Vdc	
Collector Cutoff Current ($V_{CE} = -30\text{ Vdc}$, $V_{EB(off)} = -0.5\text{ Vdc}$)	I_{CEX}	–	-50	nAdc	
Collector Cutoff Current ($V_{CB} = -50\text{ Vdc}$, $I_E = 0$) ($V_{CB} = -50\text{ Vdc}$, $I_E = 0$, $T_A = 150^\circ\text{C}$)	I_{CBO}	– –	-0.01 -10	μAdc	
Base Current ($V_{CE} = -30\text{ Vdc}$, $V_{EB(off)} = -0.5\text{ Vdc}$)	I_B	–	-50	nAdc	
ON CHARACTERISTICS					
DC Current Gain ($I_C = -0.1\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) ($I_C = -1.0\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) ($I_C = -10\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) ($I_C = -150\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) (Note 1) ($I_C = -500\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) (Note 1)	h_{FE}	75 100 100 100 50	– – – 300 –	–	
Collector – Emitter Saturation Voltage (Note 1) ($I_C = -150\text{ mAdc}$, $I_B = -15\text{ mAdc}$) ($I_C = -500\text{ mAdc}$, $I_B = -50\text{ mAdc}$)	$V_{CE(sat)}$	– –	-0.4 -1.6	Vdc	
Base – Emitter Saturation Voltage (Note 1) ($I_C = -150\text{ mAdc}$, $I_B = -15\text{ mAdc}$) ($I_C = -500\text{ mAdc}$, $I_B = -50\text{ mAdc}$)	$V_{BE(sat)}$	– –	-1.3 -2.6	Vdc	
SMALL – SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (Notes 1 and 2), ($I_C = -50\text{ mAdc}$, $V_{CE} = -20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	200	–	MHz	
Output Capacitance ($V_{CB} = -10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	8.0	pF	
Input Capacitance ($V_{EB} = -2.0\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	–	30	pF	
SWITCHING CHARACTERISTICS					
Turn-On Time	$(V_{CC} = -30\text{ Vdc}$, $I_C = -150\text{ mAdc}$, $I_{B1} = -15\text{ mAdc}$) (Figures 1 and 5)	t_{on}	–	45	ns
Delay Time		t_d	–	10	ns
Rise Time		t_r	–	40	ns
Turn-Off Time	$(V_{CC} = -6.0\text{ Vdc}$, $I_C = -150\text{ mAdc}$, $I_{B1} = I_{B2} = 15\text{ mAdc}$) (Figure 2)	t_{off}	–	100	ns
Storage Time		t_s	–	80	ns
Fall Time		t_f	–	30	ns

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.

MPS2907A Series

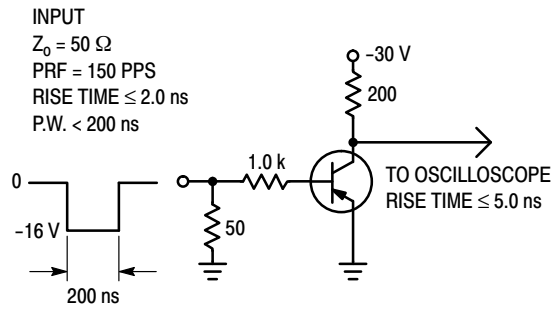


Figure 1. Delay and Rise Time Test Circuit

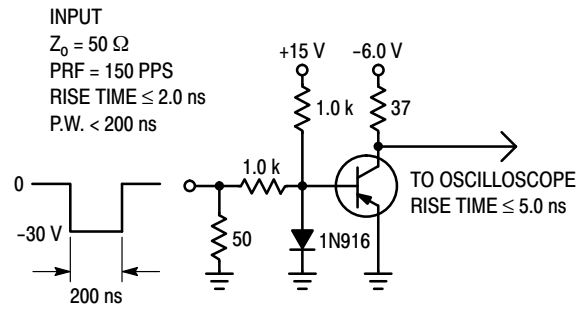


Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

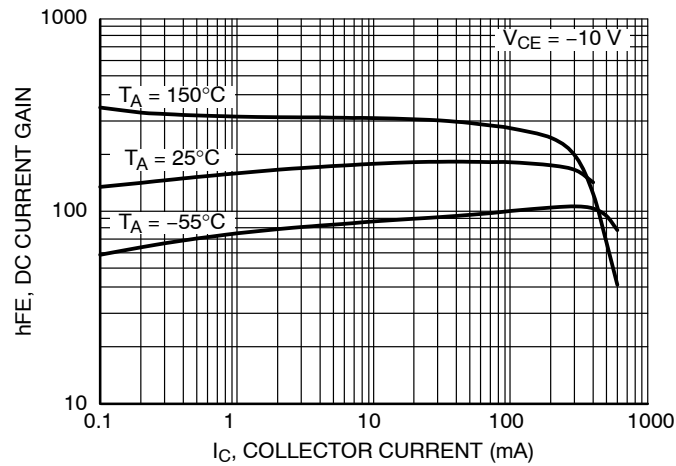


Figure 3. DC Current Gain

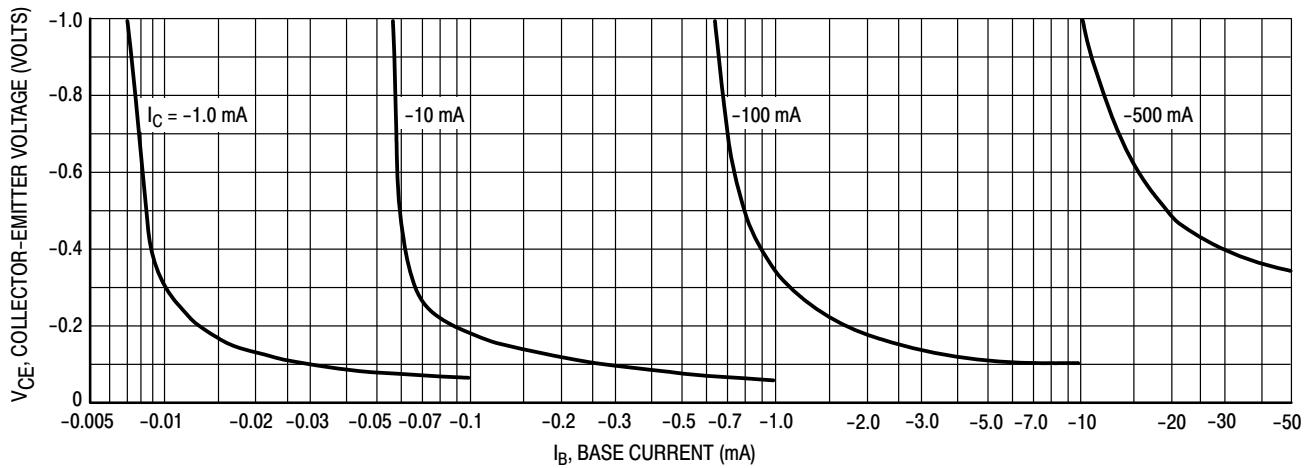


Figure 4. Collector Saturation Region

MPS2907A Series

ORDERING INFORMATION

Device	Package	Shipping [†]
MPS2907AG	TO-92 (Pb-Free)	5000 Units / Bulk
MPS2907ARLG	TO-92 (Pb-Free)	2000 / Tape & Reel
MPS2907ARLRAG	TO-92 (Pb-Free)	
MPS2907ARLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

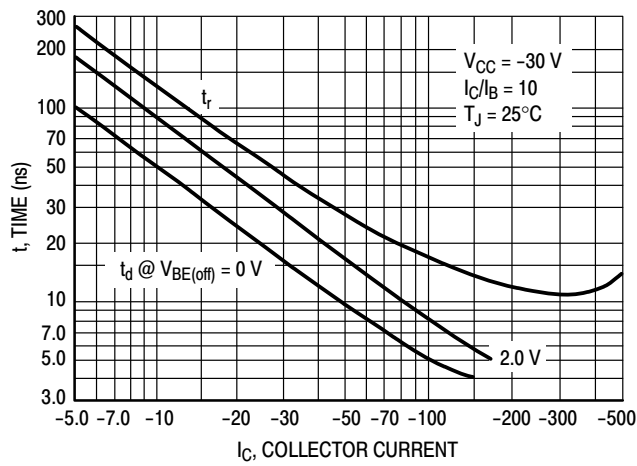


Figure 5. Turn-On Time

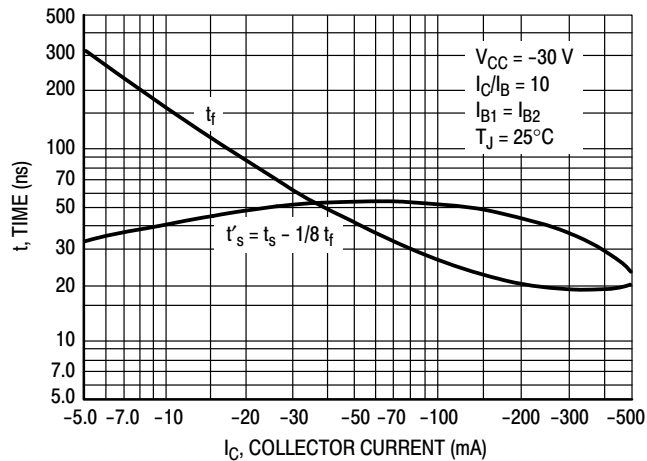


Figure 6. Turn-Off Time

MPS2907A Series

TYPICAL SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

$V_{CE} = 10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$

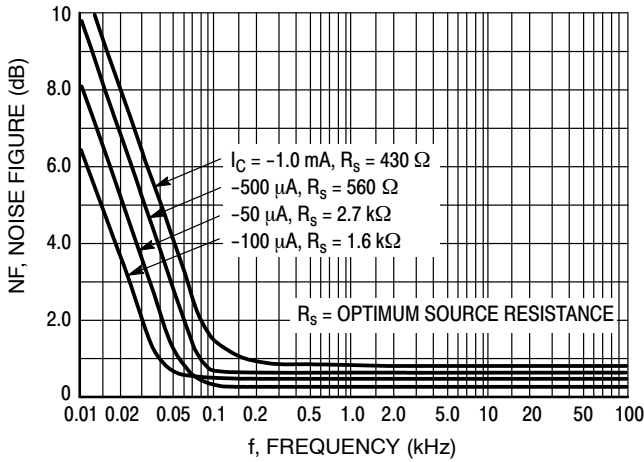


Figure 7. Frequency Effects

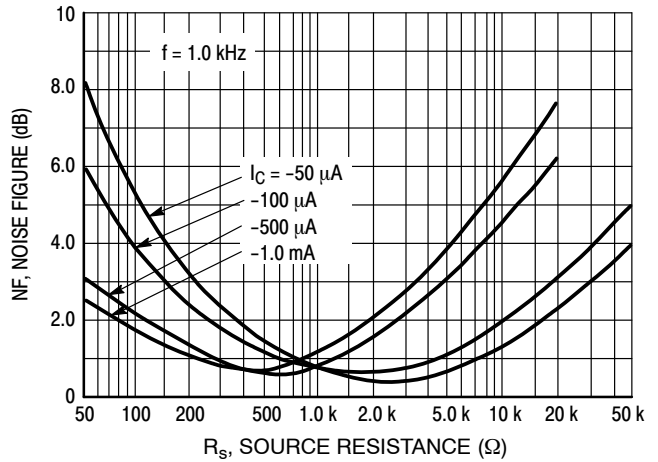


Figure 8. Source Resistance Effects

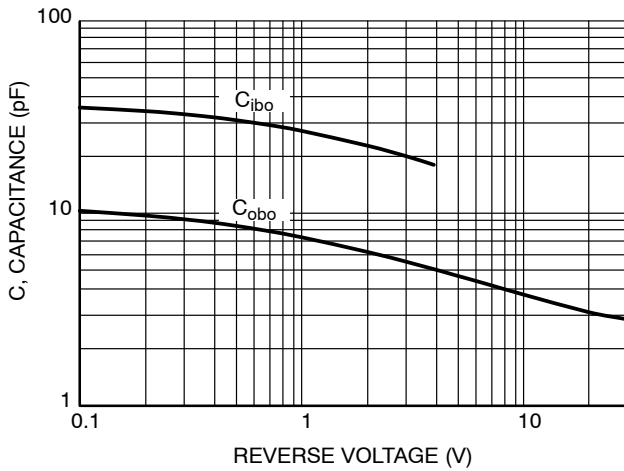


Figure 9. Capacitances

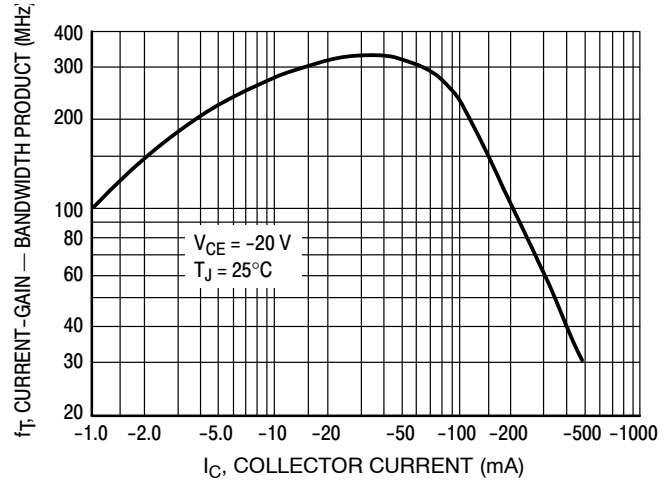


Figure 10. Current-Gain - Bandwidth Product

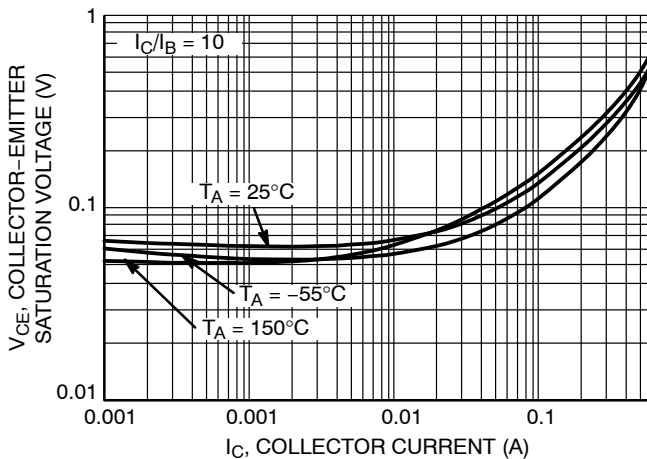


Figure 11. Collector-Emitter Saturation Voltage vs. Collector Current

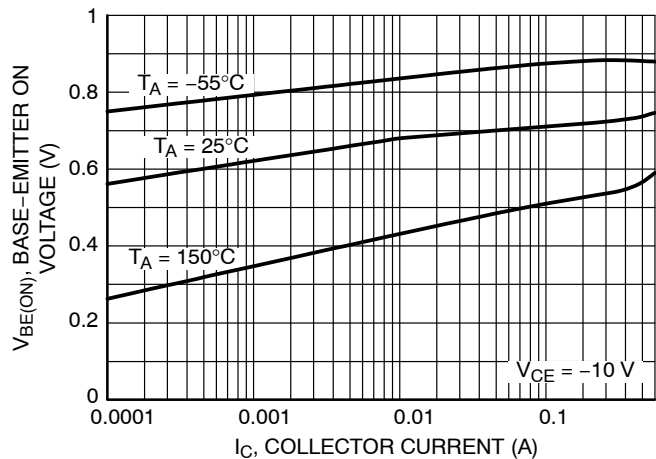


Figure 12. Base-Emitter Turn-ON Voltage vs. Collector Current

MPS2907A Series

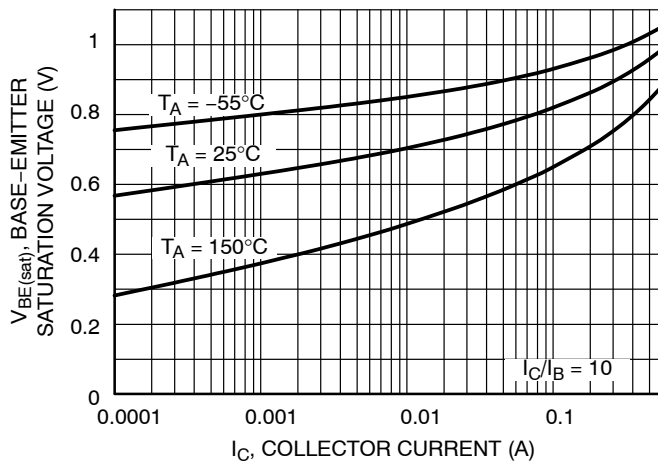


Figure 13. Base Emitter Saturation Voltage vs. Collector Current

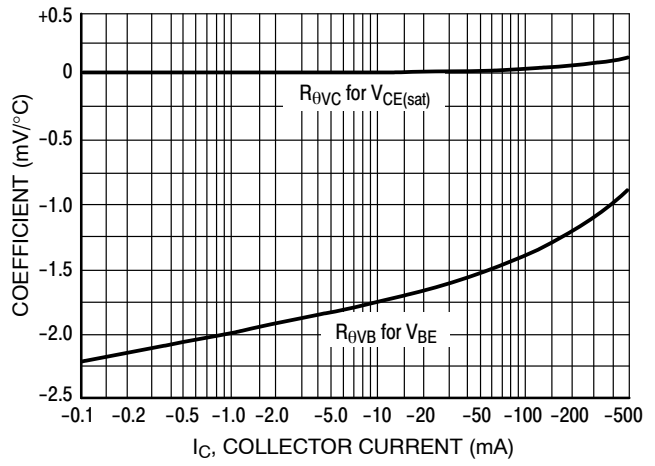


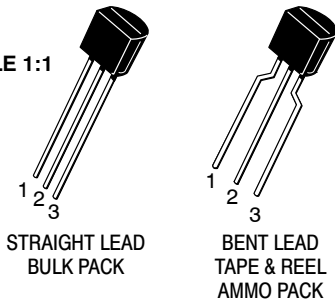
Figure 14. Temperature Coefficients

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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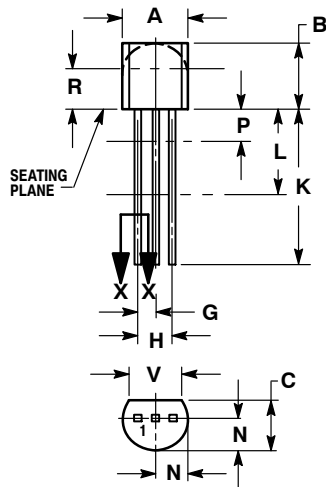
ON

SCALE 1:1

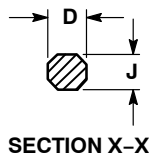


TO-92 (TO-226)
CASE 29-11
ISSUE AM

DATE 09 MAR 2007



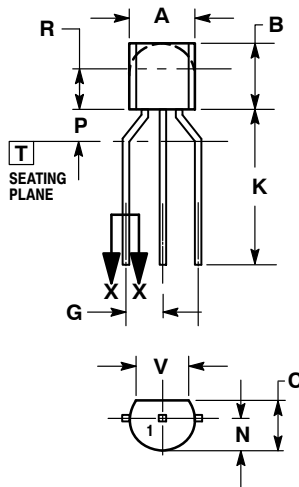
STRAIGHT LEAD
BULK PACK



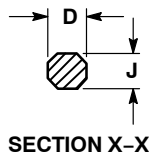
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLES ON PAGE 2

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CASE 29-11
ISSUE AM

DATE 09 MAR 2007

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE
STYLE 6: PIN 1. GATE 2. SOURCE & SUBSTRATE 3. DRAIN	STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 8: PIN 1. DRAIN 2. GATE 3. SOURCE & SUBSTRATE	STYLE 9: PIN 1. BASE 1 2. EMITTER 3. BASE 2	STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 11: PIN 1. ANODE 2. CATHODE & ANODE 3. CATHODE	STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2	STYLE 13: PIN 1. ANODE 1 2. GATE 3. CATHODE 2	STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE	STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2
STYLE 16: PIN 1. ANODE 2. GATE 3. CATHODE	STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER	STYLE 18: PIN 1. ANODE 2. CATHODE 3. NOT CONNECTED	STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE	STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE
STYLE 21: PIN 1. COLLECTOR 2. EMITTER 3. BASE	STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN	STYLE 23: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE	STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2
STYLE 26: PIN 1. V_{CC} 2. GROUND 2 3. OUTPUT	STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT	STYLE 28: PIN 1. CATHODE 2. ANODE 3. GATE	STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE	STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE
STYLE 31: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 32: PIN 1. BASE 2. COLLECTOR 3. EMITTER	STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT	STYLE 34: PIN 1. INPUT 2. GROUND 3. LOGIC	STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

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